

Serial No. 10/781,786

Docket No.: 300.1145

IN THE CLAIMS:

The text of all pending claims, (including withdrawn claims) is set forth below. Cancelled and not entered claims are indicated with claim number and status only. The claims as listed below show added text with underlining and deleted text with ~~striketrough~~. The status of each claim is indicated with one of (original), (currently amended), (cancelled), (withdrawn), (new), (previously presented), or (not entered).

Please CANCEL claims 1-7, 9, 11 and 12; AMEND claims 8 and 10 in accordance with the following:

1. (CANCELLED)

2. (CANCELLED)

3. (CANCELLED)

4. (CANCELLED)

5. (CANCELLED)

6. (CANCELLED)

7. (CANCELLED)

8. (CURRENTLY AMENDED) A method of using a semiconductor device, said device comprising a substrate body; a plurality of external contact terminals formed of springy wires, said external terminals arranged on and extending from said substrate body; each of said external contact terminals having a base end connected to said substrate body and a tip end apart from said base end; and each of said external contact terminals being plated on at least said tip end thereof with a film of multiple successively plated layers which are selectively removable by an etching treatment; ~~the~~ said method comprising:

selectively removing one or more of said layers of said plated film by an etching treatment in accordance with a degree of contamination of the tip end, wherein:

an outermost layer of the successively plated layers is dissolvable by a first etching agent but is not reactive to a second etching agent, and a next most outermost layer is dissolvable by the second etching agent but is not reactive to the first etching

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agent, andsaid selectively removing comprises using the first etching agent to remove the
outmost layer, andrinsing this the semiconductor device to enable reuse of the same.

9. (CANCELLED)

10. (CURRENTLY AMENDED) A method of using a semiconductor device comprising a substrate body, a plurality of external contact terminals formed of springy wires arranged on and extending from said substrate body, each of said external contact terminals having a base end connected to said substrate body and a tip end apart from said base end, and each of said external contact terminals being plated, at least on said tip end thereof, with a multiple-layered film which is selectively removable by an etching treatment; said method comprising:

selectively removing one or more layers of said multiple-layered, plated film by an etching treatment in accordance with a degree of contamination of the tip end; wherein, when the first outermost layer has been selectively removed by a first etching agent, removing the next most outermost layer by using a second etching agent; and

rinsing the semiconductor device subsequently to the etching treatment to enable reuse of the same.

11. (CANCELLED)

12. (CANCELLED)

13. (PREVIOUSLY PRESENTED) A method of using a semiconductor device, said device as set forth in claim 8, further comprising: a substrate body, a plurality of external contact terminals formed of springy wires, said external terminals arranged on and extending from said substrate body, each of said external contact terminals having a base end connected to said substrate body and a tip end apart from said base end; and each of said external contact terminals being plated on at least said tip end thereof with a film of multiple successively plated layers which are selectively removable by an etching treatment, said method comprising:
selectively removing one or more of said layers of said plated film by an etching treatment in accordance with a degree of contamination of the tip end, and

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following selective removal of all of the successively plated layers, replating each of the plurality of external contact terminals with a ~~multiple-layered film~~ of selectively plated and selectively removable, multiple layers, by respective, first and second etching agents, for reuse of the semiconductor device and associated plurality of external contact terminals.